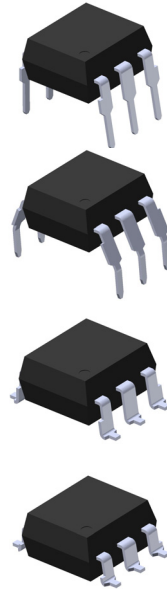


6 PIN DIP PHOTOTRANSISTOR PHOTOCOUPLER

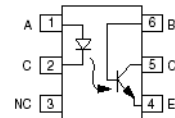
CNY17-X Series CNY17F-X Series

Features

- Current transfer ratios in selected narrow range groups
CNY17-1, CNY17F-1: 40-80%
CNY17-2, CNY17F-2: 63-125%
CNY17-3, CNY17F-3: 100-200%
CNY17-4, CNY17F-4: 160-320%
- High isolation voltage between input and output
(Viso = 5000 Vrms)
- Creepage distance > 7.6 mm
- Operating temperature up to +110°C
- The CNY17F-X series offers no external base connection for minimum noise susceptibility
- Compact dual-in-line package
- Pb free and RoHS compliant.
- UL approved (No. E214129)
- VDE approved (No. 132249)
- SEMKO approved
- NEMKO approved
- DEMKO approved
- FIMKO approved
- CSA approved

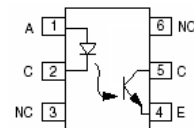


Schematic



CNY17-X

1. Anode
2. Cathode
3. No Connection
4. Emitter
5. Collector
6. Base



CNY17F-X

1. Anode
2. Cathode
3. No Connection
4. Emitter
5. Collector
6. No Connection

Description

The CNY17-X and CNY17F-X series of devices each consist of an infrared emitting diode optically coupled to a phototransistor.

It is packaged in a 6-pin DIP package and available in wide-lead spacing and SMD option.

Applications

- Power supply regulators
- Digital logic inputs
- Microprocessor inputs

6 PIN DIP PHOTOTRANSISTOR PHOTOCOUPLER

CNY17-X Series CNY17F-X Series

Absolute Maximum Ratings ($T_a=25^{\circ}\text{C}$)

Parameter		Symbol	Rating	Unit
Input	Forward current	I_F	60	mA
	Peak forward current ($t = 10\mu\text{s}$)	I_{FM}	1	A
	Reverse voltage	V_R	6	V
	Power dissipation ($T_A = 25^{\circ}\text{C}$)	P_D	100	mW
	Derating factor (above 100°C)		3.8	mW/ $^{\circ}\text{C}$
Output	Collector-Emitter voltage	V_{CEO}	80	V
	Collector-Base voltage ^{*1}	V_{CBO}	80	V
	Collector current	I_C	50	mA
	Emitter-Collector voltage	V_{ECO}	7	V
	Power dissipation ($T_A = 25^{\circ}\text{C}$)	P_C	150	mW
	Derating factor (above 100°C)		9.0	mW/ $^{\circ}\text{C}$
Total power dissipation		P_{tot}	200	mW
Isolation voltage ^{*2}		V_{iso}	5000	Vrms
Operating temperature		T_{opr}	-55~+110	$^{\circ}\text{C}$
Storage temperature		T_{stg}	-55~+125	$^{\circ}\text{C}$
Soldering temperature ^{*3}		T_{sol}	260	$^{\circ}\text{C}$

Notes

*1 Only for CNY17-X series.

*2 AC for 1 minute, R.H.= 40 ~ 60% R.H. In this test, pins 1, 2 & 3 are shorted together, and pins 4, 5 & 6 are shorted together.

*3 For 10 seconds.

6 PIN DIP PHOTOTRANSISTOR PHOTOCOUPLER

CNY17-X Series CNY17F-X Series

Electrical Characteristics ($T_a=25^{\circ}\text{C}$ unless specified otherwise)

Input

Parameter	Symbol	Min.	Typ.*	Max.	Unit	Condition
Forward voltage	V_F	-	-	1.65	V	$I_F = 60\text{mA}$
Reverse current	I_R	-	-	10	μA	$V_R = 6\text{V}$
Input capacitance	C_{in}	-	18	-	pF	$V = 0, f = 1\text{MHz}$

Output

Parameter	Symbol	Min.	Typ.*	Max.	Unit	Condition
Collector-Base dark current	I_{CBO}	-	-	20	nA	$V_{CB} = 10\text{V}, I_F = 0\text{mA}$
Collector-Emitter dark current	I_{CEO}	-	-	50	nA	$V_{CE} = 10\text{V}, I_F = 0\text{mA}$
Collector-Emitter breakdown voltage	BV_{CEO}	80	-	-	V	$I_C = 1\text{mA}, I_F = 0\text{mA}$
Collector-Base breakdown voltage	BV_{CBO}	80	-	-	V	$I_C = 0.1\text{mA}, I_F = 0\text{mA}$
Emitter-Collector breakdown voltage	BV_{ECO}	7	-	-	V	$I_E = 0.1\text{mA}, I_F = 0\text{mA}$
Collector-Emitter capacitance	C_{CE}	-	8	-	pF	$V_{CE} = 0\text{V}, f = 1\text{MHz}$

* Typical values at $T_a = 25^{\circ}\text{C}$

6 PIN DIP PHOTOTRANSISTOR PHOTOCOUPLER

CNY17-X Series CNY17F-X Series

Transfer Characteristics ($T_a=25^{\circ}\text{C}$ unless specified otherwise)

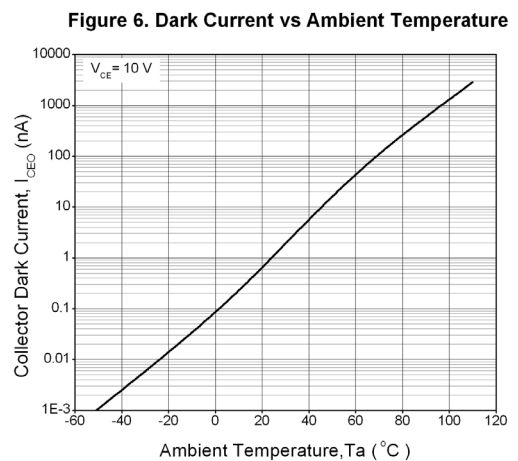
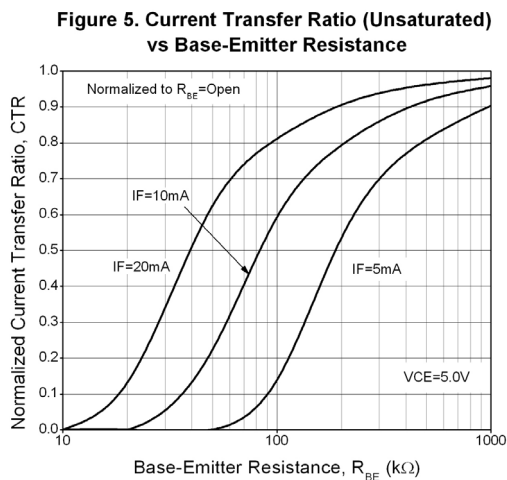
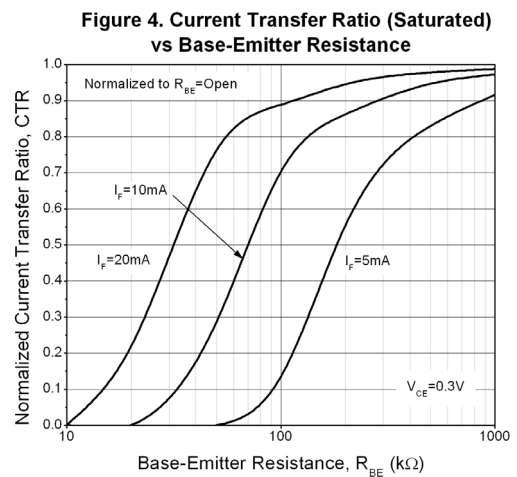
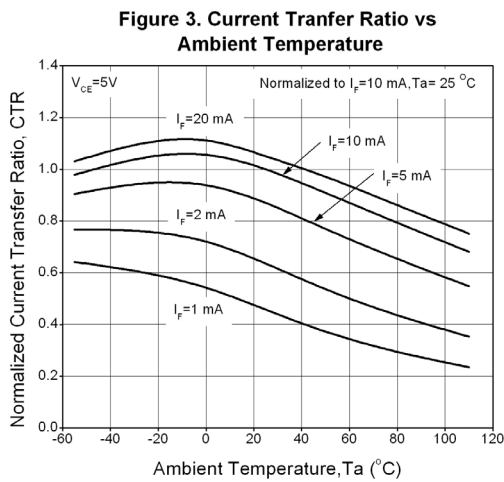
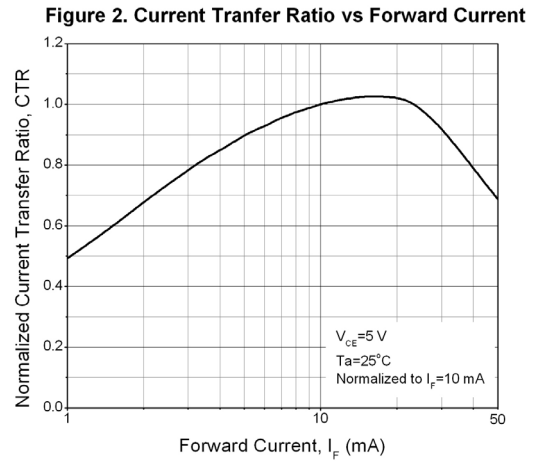
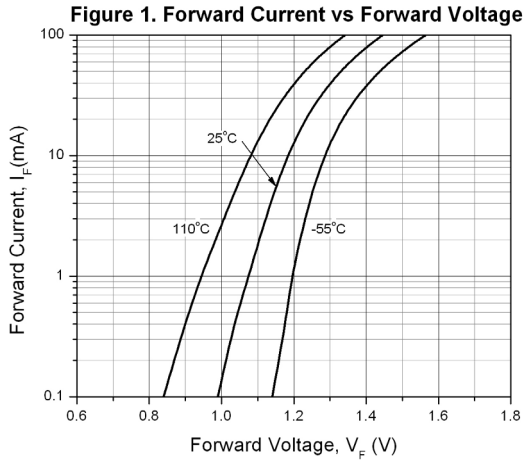
Parameter		Symbol	Min.	Typ.*	Max.	Unit	Condition
Current Transfer Ratio	CNY17-1 CNY17F-1	CTR	40	-	80	%	$I_F = 10\text{mA}$, $V_{CE} = 5\text{V}$
	CNY17-2 CNY17F-2		63	-	125		
	CNY17-3 CNY17F-3		100	-	200		
	CNY17-4 CNY17F-4		160	-	320		
Current Transfer Ratio	CNY17-1 CNY17F-1	CTR	13	-	-	%	$I_F = 1\text{mA}$, $V_{CE} = 5\text{V}$
	CNY17-2 CNY17F-2		22	-	-		
	CNY17-3 CNY17F-3		34	-	-		
	CNY17-4 CNY17F-4		56	-	-		
Collector-Emitter saturation voltage		$V_{CE(sat)}$	-	-	0.3	V	$I_F = 10\text{mA}$, $I_C = 2.5\text{mA}$
Isolation resistance		R_{IO}	10^{11}	-	-	Ω	$V_{IO} = 500\text{Vdc}$
Input-output capacitance		C_{IO}	-	0.5	-	pF	$V_{IO} = 0$, $f = 1\text{MHz}$
Turn-on time		T_{on}	-	10	12	μs	$V_{CC} = 10\text{V}$, $I_C = 2\text{mA}$, $R_L = 100\Omega$ See Fig. 11
Turn-off time		T_{off}	-	9	12		
Rise time		T_r	-	6	10		
Fall time		T_f	-	8	10		
Rise time		T_r	-	2	10		$V_{CC} = 5\text{V}$, $I_F = 10\text{mA}$, $R_L = 75\Omega$, See Fig. 11
Fall time		T_f	-	3	10		

* Typical values at $T_a = 25^{\circ}\text{C}$

6 PIN DIP PHOTOTRANSISTOR PHOTOCOUPLER

CNY17-X Series CNY17F-X Series

Typical Performance Curves



6 PIN DIP PHOTOTRANSISTOR PHOTOCOUPLER

CNY17-X Series CNY17F-X Series

Figure 7. Collector-Emitter Saturation Voltage vs Collector Current

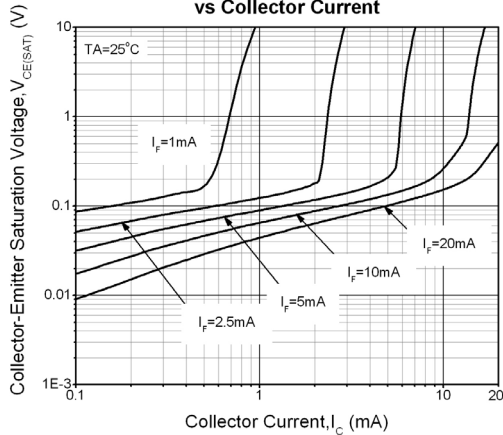


Figure 8. Switching Time vs Load Resistance

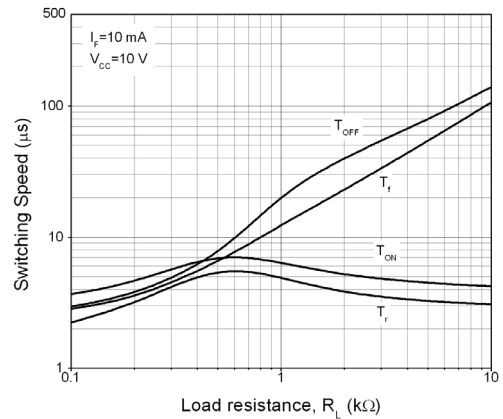


Figure 9. Turn-on Time vs Base-Emitter Resistance

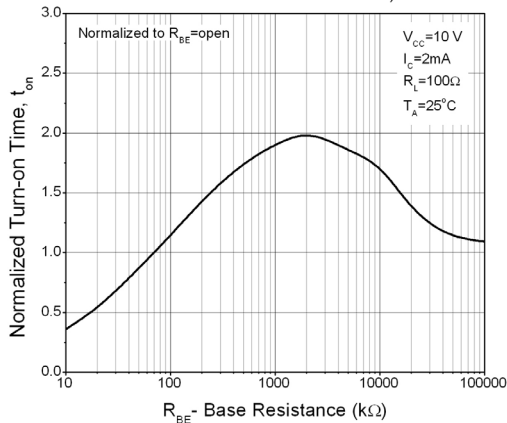


Figure 10. Turn-off Time vs Base-Emitter Resistance

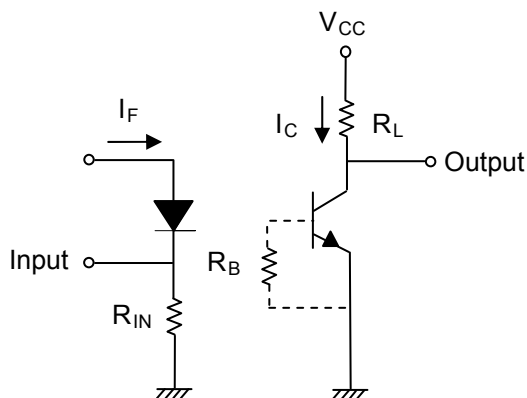
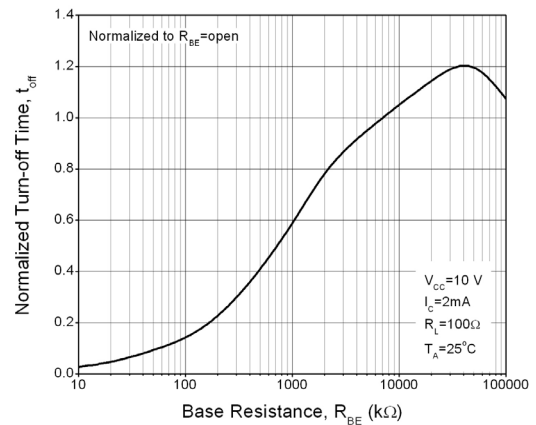


Figure 11. Switching Time Test Circuit & Waveforms

6 PIN DIP PHOTOTRANSISTOR PHOTOCOUPLER

CNY17-X Series
CNY17F-X Series

Order Information

Part Number

CNY17-XY(Z)-V

or

CNY17F-XY(Z)-V

Note

- X = Part no. (1, 2, 3 or 4)
Y = Lead form option (S, S1, M or none)
Z = Tape and reel option (TA, TB or none).
V = VDE (optional)

Option	Description	Packing quantity
None	Standard DIP-6	65 units per tube
M	Wide lead bend (0.4 inch spacing)	65 units per tube
S (TA)	Surface mount lead form + TA tape & reel option	1000 units per reel
S (TB)	Surface mount lead form + TB tape & reel option	1000 units per reel
S1 (TA)	Surface mount lead form (low profile) + TA tape & reel option	1000 units per reel
S1 (TB)	Surface mount lead form (low profile) + TB tape & reel option	1000 units per reel

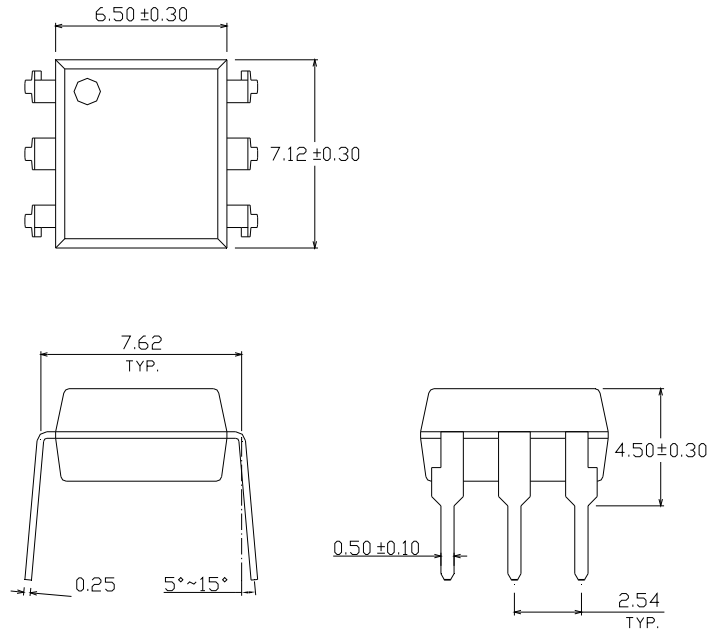
6 PIN DIP PHOTOTRANSISTOR PHOTOCOUPLER

**CNY17-X Series
CNY17F-X Series**

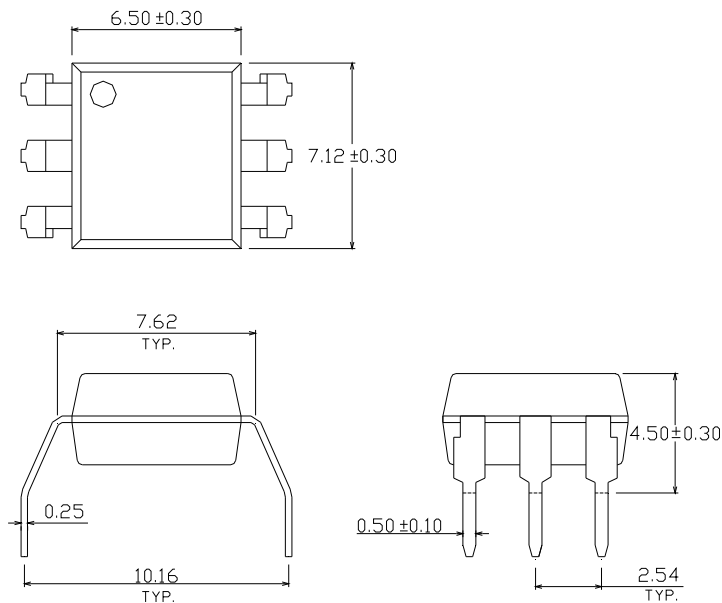
Package Drawings

(Dimensions in mm)

Standard DIP Type



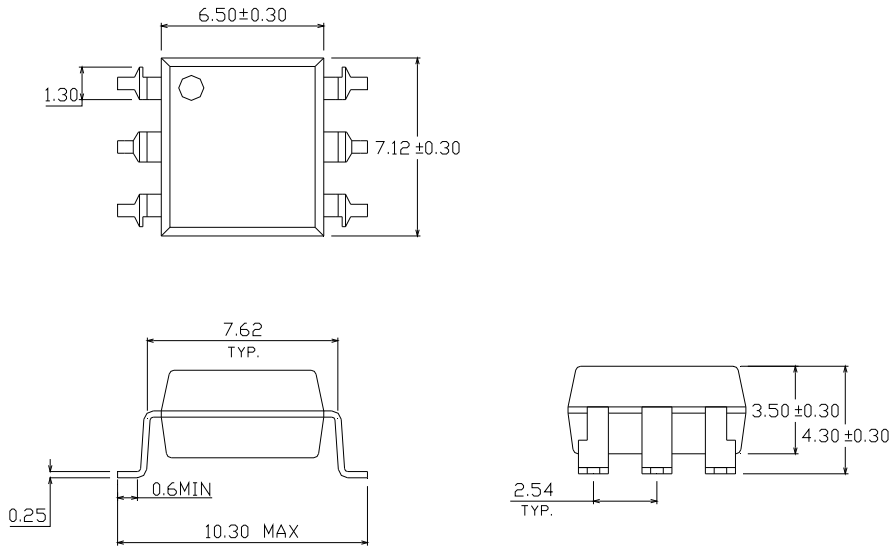
Option M Type



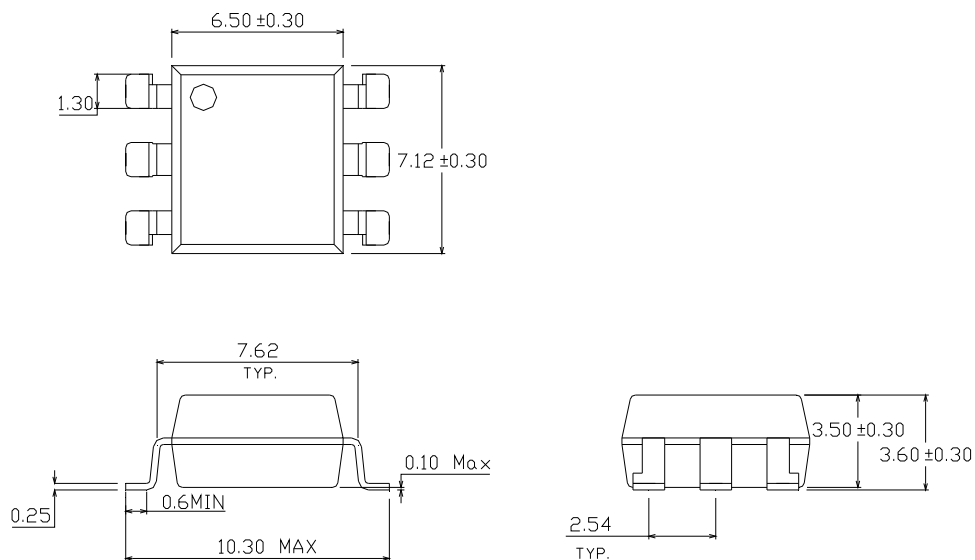
6 PIN DIP PHOTOTRANSISTOR PHOTOCOUPLER

**CNY17-X Series
CNY17F-X Series**

Option S Type



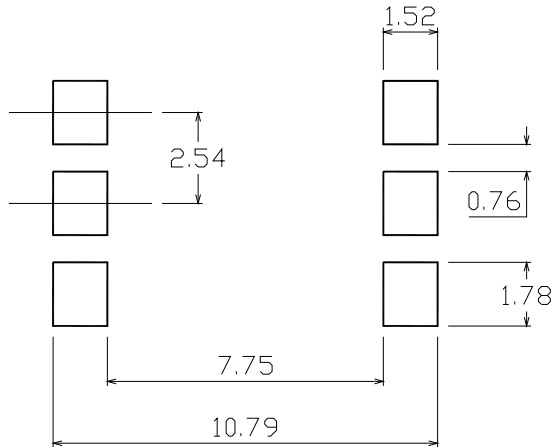
Option S1 Type



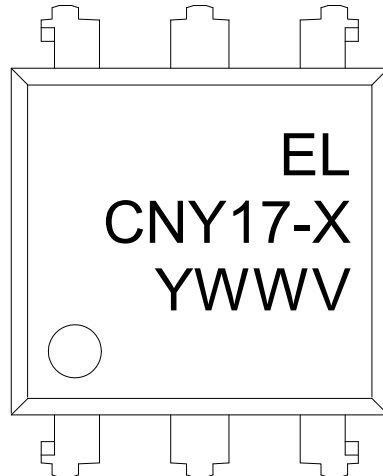
6 PIN DIP PHOTOTRANSISTOR PHOTOCOUPLER

**CNY17-X Series
CNY17F-X Series**

Recommended pad layout for surface mount leadform



Device Marking



Notes

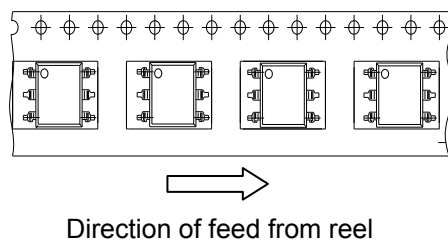
- EL denotes Everlight
- CNY17-X denotes Device Number (X: 1, 2, 3 or 4)
- Y denotes 1 digit Year code
- WW denotes 2 digit Week code
- V denotes VDE (optional)

6 PIN DIP PHOTOTRANSISTOR PHOTOCOUPLER

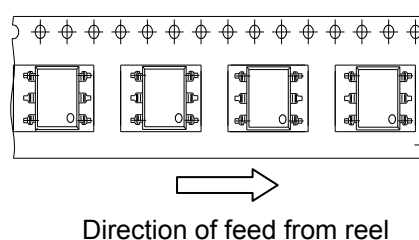
**CNY17-X Series
CNY17F-X Series**

Tape & Reel Packing Specifications

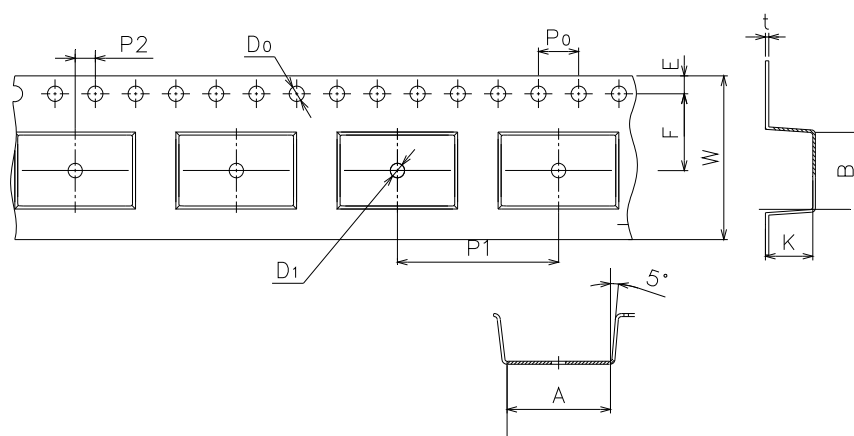
Option TA



Option TB



Tape dimensions



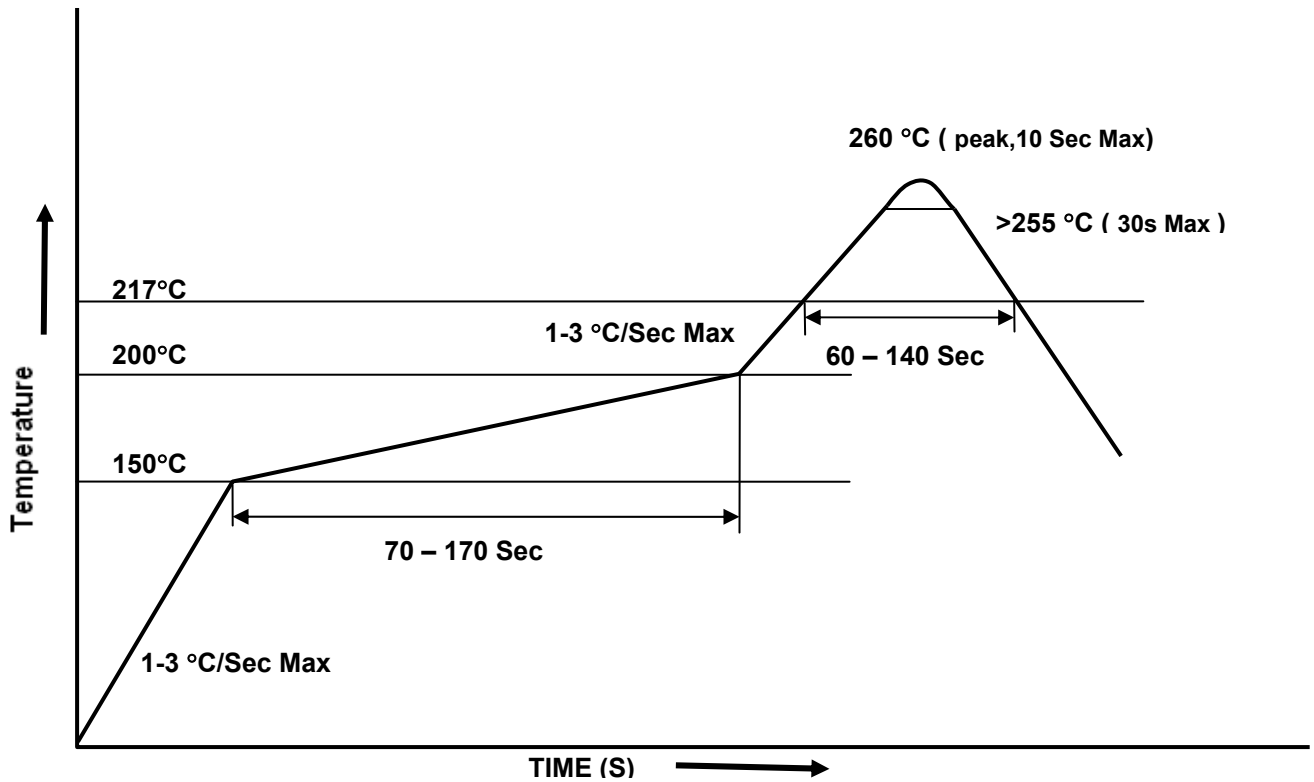
Dimension No.	A	B	Do	D1	E	F
Dimension (mm)	10.4±0.1	7.52±0.1	1.5±0.1	1.5+0.1/-0	1.75±0.1	7.5±0.1

Dimension No.	Po	P1	P2	t	W	K
Dimension (mm)	4.0±0.15	16.0±0.1	2.0±0.1	0.35±0.03	16.0±0.2	4.5±0.1

6 PIN DIP PHOTOTRANSISTOR PHOTOCOUPLER

**CNY17-X Series
CNY17F-X Series**

Solder Reflow Temperature Profile



6 PIN DIP PHOTOTRANSISTOR PHOTOCOUPLER

**CNY17-X Series
CNY17F-X Series**

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